

Application Serial No: 10/572,861
Responsive to the Office Action mailed on: April 5, 2007

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IN THE CLAIMS

Amendments To The Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A chip type-LED comprising an insulating substrate, a light emitting diode chip mounted on an upper surface of the insulating substrate, and a transparent package provided on the upper surface of the insulating substrate to seal the light emitting diode chip,

wherein the light emitting diode chip is mounted on the upper surface of the insulating substrate with an anode electrode of the chip oriented downward and with located closer to the insulating substrate than a cathode electrode of the chip oriented upward so that the anode is located between the cathode and the insulating substrate; and

wherein the light emitting diode chip includes a diode substrate and a light emitting layer between the anode and the cathode, the light emitting layer being located closer to the cathode than to the anode, the diode substrate being located between the cathode and the light emitting layer for preventing light generated at the light emitting layer from being emitted through the cathode.

2. (Currently Amended) The chip type-LED according to claim 1, wherein the light emitting diode chip ~~further includes a light emitting layer arranged adjacent to the cathode electrode of the chip and also includes a side surface inclined inwardly as the side surface extends from the cathode electrode toward the anode electrode.~~

3. (Currently Amended) The chip type-LED according to claim 1, wherein the upper surface of the insulating substrate is formed with a white color film at least around the light emitting diode chip.

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4. (New) The chip LED according to claim 1, wherein the light emitting chip further includes a n-type semiconductor layer located between the diode substrate and the light emitting layer, and a p-type semiconductor layer located between the anode and the light emitting layer, the p-type semiconductor layer having a greater thickness than the n-type semiconductor layer.